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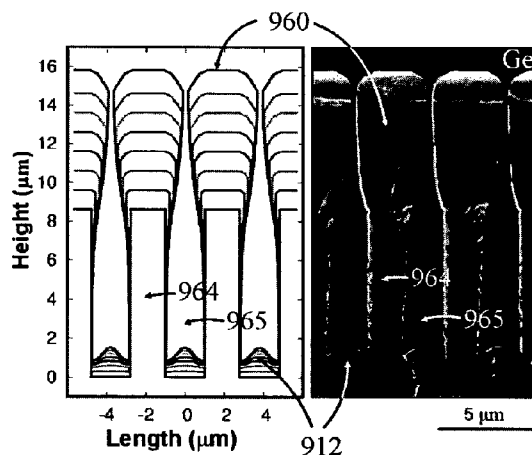
(54) Title: DISLOCATION AND STRESS MANAGEMENT BY MASK-LESS PROCESSES USING SUBSTRATE PATTERN-
ING AND METHODS FOR DEVICE FABRICATION

Fig. 9(e)

(57) Abstract: Structures and methods for producing active layer stacks of lattice matched, lattice mismatched and thermally mis-
matched semiconductor materials, with low threading dislocation densities, no layer cracking and minimized wafer bowing, by us-
ing epitaxial growth onto elevated substrate regions in a mask-less process.